



High-end Power Semiconductor Manufacturer

ZK1200A 2100-3000V

Fast Recovery Diode

- Low switching losses
- Low reverse recovery charge High
- power cycling capability



Average forward current		I_{FAV}		1208 A		
Repetitive peak reverse voltage		V_{RRM}		2100 – 3000 V		
Reverse recovery time		t_{rr}		7.00 μ s		
V_{RRM} , V	2100	2200	2400	2600	2800	3000
Voltage code	21	22	24	26	28	30
T_j , °C	– 60 – 150					

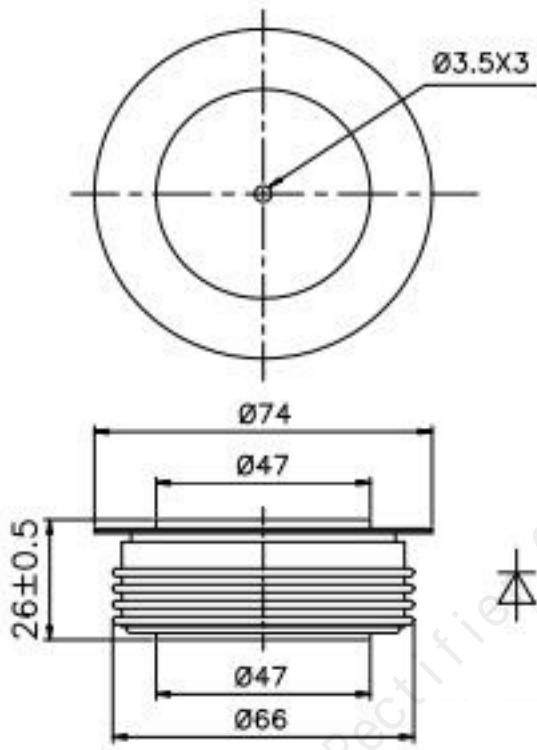
MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	Values	Test conditions	
ON-STATE					
I_{FAV}	Average forward current	A	1208	$T_c=85$ °C; Double side cooled; 180° half-sine wave; 50 Hz	
I_{FSM}	Surge forward current	kA	16.0	$T_j=T_{j \max}$	180° half-sine wave; $t_p=10$ ms; $V_R=0.6V_{RRM}$
I^2t	Safety factor	$A^2 \cdot 10^3$	1280	$T_j=T_{j \max}$	180° half-sine wave; $t_p=10$ ms; $V_R=0.6V_{RRM}$
BLOCKING					
V_{RRM}	Repetitive peak reverse voltages	V	2100–3000	$t_p=10$ ms	
V_R	Reverse continuous voltages	V	$0.6V_{RRM}$	$T_j=T_{j \max}$;	
THERMAL					
T_{stg}	Storage temperature	°C	–40–160		
T_j	Operating junction temperature	°C	–60 –150		
MECHANICAL					
F	Mounting force	kN	19 – 26		

CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions
ON-STATE				
V _{FM}	Peak forward voltage, max	V	2.80	T _j =25 °C; I _{TM} =1500A, F=24.0kN
V _{F(TO)}	Forward threshold voltage, max	V	1.62	
r _T	Forward slope resistance, max	mΩ	0.36	T _j =T _{j max} ;
BLOCKING				
I _{RRM}	Repetitive peak reverse current, max	mA	100	T _j =T _{j max} ; V _R =V _{RRM}
SWITCHING				
Q _{rr}	Total recovered charge, max	μC	650	I _{TM} =2000A, t _p =1000μs, -di/dt=60A/μs,
t _{rr}	Reverse recovery time ¹⁾ , max	μs	7.00	V _R =50V
THERMAL				
R _{thjc}	Thermal resistance, junction to case, max	°C/W	0.0200	Clamping force 24.0kN Double side cooled
R _{thck}	Thermal resistance, case to heatsink, max	°C/W	0.0050	Clamping force 24.0kN Double side cooled
MECHANICAL				
w	Weight, max	g	440	

OVERALL DIMENSIONS



ZT55

All dimensions in millimeters